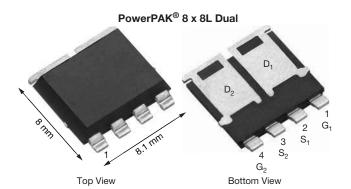
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ISHA

Vishay Siliconix

Automotive Dual N-Channel 80 V (D-S) 175 °C MOSFET



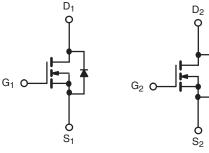
PRODUCT SUMMARY	
V _{DS} (V)	80
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.0135
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.0170
I _D (A) per leg	36
Configuration	Dual
Package	PowerPAK 8 x 8L

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Fully lead (Pb)-free device
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS COMPLIANT HALOGEN FREE



N-Channel MOSFET



ABSOLUTE MAXIMUM RATINGS (T _C =	= 25 °C, unles	s otherwise noted	l)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	80	V
Gate-source voltage		V _{GS}	± 20	v
Continuous drain current	$T_C = 25 \ ^\circ C \ ^a$	1	36	
	T _C = 125 °C	I _D	21	
Continuous source current (diode conduction) ^a		I _S	34	А
Pulsed drain current ^b		I _{DM}	128	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	27	
Single pulse avalanche energy	L = 0.1 mm	E _{AS}	36	mJ
Maximum power dissipation ^b	T _C = 25 °C	Р	187	w
Maximum power dissipation ~	T _C = 125 °C	P _D	62	٧V
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) d, e			260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R _{thJA}	100	°C/W
Junction-to-case (drain)		R _{thJC}	4.0	C/W

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

c. When mounted on 1" square PCB (FR4 material)

d. See solder profile (www.vishay.com/doc?73257). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

1

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	•	-					
Drain-source breakdown voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	80	-	-	v
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	- V _{GS} , I _D = 250 μΑ	1.5	2	2.5	v
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20$ V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 20 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 80 V, T _J = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V _{DS} = 80 V, T _J = 175 °C	-	-	150	
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	40	-	-	Α
		$V_{GS} = 10 V$	I _D = 5 A	-	0.0036	0.0135	
Durin country on state mariatements		$V_{GS} = 4.5 V$	I _D = 5 A	-	0.0045	0.0170	Ω
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 5 A, T _J = 125 °C	-	-	0.0220	
		V _{GS} = 10 V	I _D = 5 A, T _J = 175 °C	-	-	0.0280	
Forward Transconductance b	g fs	V _{DS}	= 15 V, I _D = 10 A	-	55	-	S
Dynamic ^b	•	•		•	•	•	•
Input capacitance	C _{iss}			-	1595	1995	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 40 V, f = 1 MHz	-	616	770	pF
Reverse transfer capacitance	C _{rss}			-	23	30	
Total gate charge ^c	Qg			-	26	36	
Gate-source charge c	Q _{gs}	$V_{GS} = 10 V$	$V_{DS} = 40 \text{ V}, I_D = 10 \text{ A}$	-	5	-	nC
Gate-drain charge ^c	Q _{gd}			-	4	-	1
Gate resistance	R _g		f = 1 MHz	0.7	1.1	1.9	Ω
Turn-on delay time ^c	t _{d(on)}			-	10	14	
Rise time ^c	t _r	V _{DD}	= 40 V, R_{L} = 4 Ω	-	3	5	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 10 \text{ A},$	$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	21	27	ns
Fall time ^c	t _f	1		-	3	5	1
Source-Drain Diode Ratings and Cha	racteristics ^b				•		
Pulsed current ^a	I _{SM}			-	-	128	Α
Forward voltage	V _{SD}	I _E :	= 40 A, V _{GS} = 0	-	1	1.2	V

Notes

a. Pulse test; pulse width $\leq 300~\mu\text{s},~\text{duty}~\text{cycle} \leq 2~\%$

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

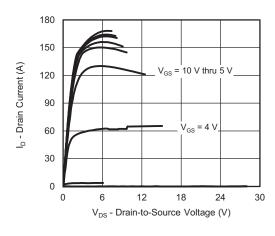
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

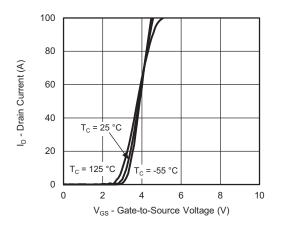


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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Output Characteristics



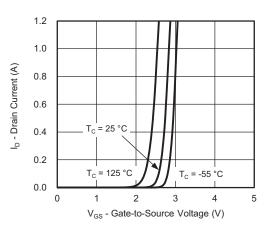
Transfer Characteristics

T_C = -55 °C

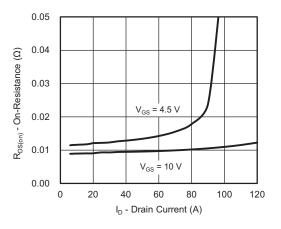
T_C = 125 °C

12

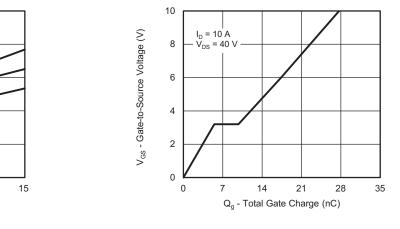
T_c = 25 °C



Transfer Characteristics



On-Resistance vs. Drain Current



Transconductance

I_D - Drain Current (A)

9

6

Capacitance

S17-0465-Rev. B, 27-Mar-17

3

100

80

60

40

20

0

g_{fs} - Transconductance (S)

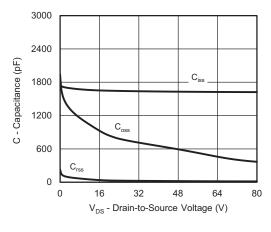
3 tions. contact: automostechsu Document Number: 76465

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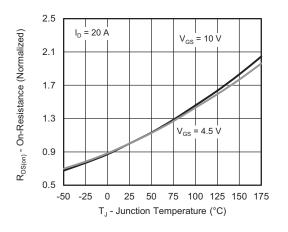


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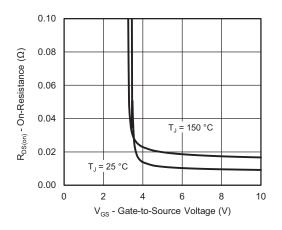
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



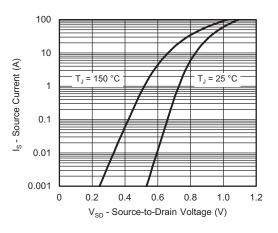
Capacitance



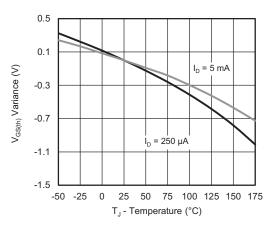
On-Resistance vs. Junction Temperature



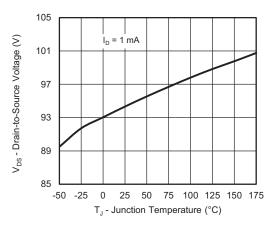
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

S17-0465-Rev. B, 27-Mar-17

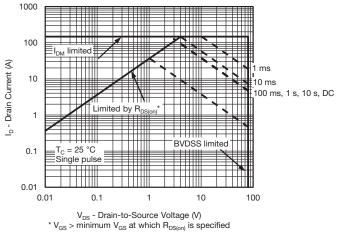
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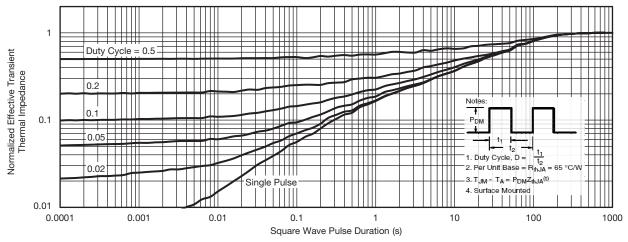


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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Safe Operating Area



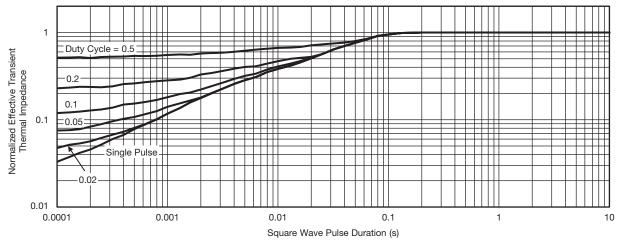
Normalized Thermal Transient Impedance, Junction-to-Ambient



Vishay Siliconix

Document Number: 76465

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

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- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction to Case (25 °C)

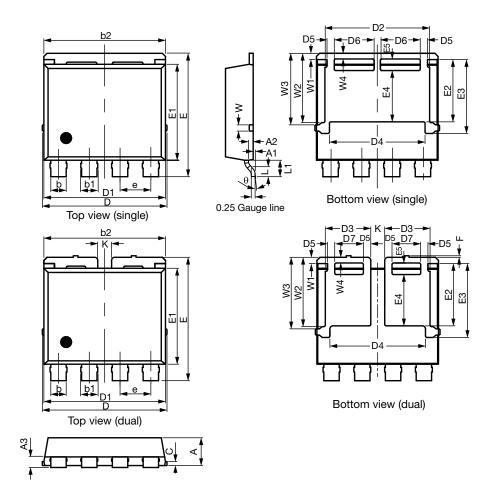
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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DIM.		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.70	1.80	1.90	0.067	0.071	0.075	
A1	0.00	0.08	0.13	0.000	0.003	0.005	
A2	0.25	0.30	0.35	0.010	0.012	0.014	
A3	0.55	0.62	0.70	0.022	0.024	0.028	
b	0.92	1.00	1.08	0.036	0.039	0.043	
b1	1.02	1.10	1.18	0.040	0.043	0.046	
b2	7.80	7.90	8.00	0.307	0.311	0.315	
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	8.00	8.10	8.25	0.315	0.319	0.325	
D1	7.80	7.90	8.00	0.307	0.311	0.315	
D2	6.70	6.80	6.90	0.264	0.268	0.272	
D3	2.85	2.95	3.05	0.112	0.116	0.120	
D4	6.11	6.21	6.31	0.241	0.244	0.248	
D5	0.37	0.47	0.57	0.015	0.019	0.022	
D6	2.49	2.59	2.69	0.098	0.102	0.106	
D7	1.76	1.86	1.96	0.069	0.073	0.077	

Revision: 16-Oct-17

Document Number: 67734

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Package Information





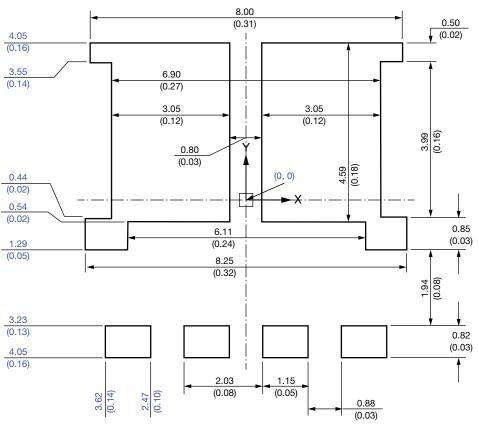
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DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
е	1.95	2.00	2.05	0.077	0.079	0.081	
Е	7.90	8.00	8.10	0.311	0.315	0.319	
E1	6.12	6.22	6.32	0.241	0.245	0.249	
E2	3.94	4.04	4.14	0.140	0.159	0.163	
E3	4.69	4.79	4.89	0.185	0.189	0.193	
E4	3.23	3.33	3.43	0.127	0.131	0.135	
E5	0.65	0.75	0.85	0.026	0.030	0.033	
F	0.00	0.10	0.15	0.000	0.004	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К	0.80	0.90	1.00	0.031	0.035	0.039	
W	0.30	0.40	0.50	0.012	0.016	0.020	
W1	0.30	0.40	0.50	0.012	0.016	0.020	
W2	4.39	4.49	4.59	0.173	0.177	0.181	
W3	4.54	4.64	4.74	0.179	0.183	0.187	
W4	0.32	0.37	0.42	0.013	0.015	0.017	
θ	6°	10°	14°	6°	10°	14°	



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Recommended Minimum PADs for PowerPAK® 8 x 8L Dual



Dimensions in millimeters (inches)

Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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